



N-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low On-Resistance
 - 110 m Ω @ V_{GS} = 4.5V
 - 145 mΩ @ V_{GS} = 2.5V
 - 230 m Ω @ V_{GS} = 1.8V
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Lead, Halogen and Antimony Free, RoHS Compliant "Green" Device (Notes 1, 2 and 3)
- Qualified to AEC-Q101 Standards for High Reliability

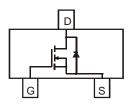
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.008 grams (approximate)





Top View



Top View Internal Schematic

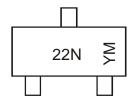
Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2230U-7	SOT23	3000/Tape & Reel

Notes:

- ${\bf 1.\ No\ purposefully\ added\ lead.\ Halogen\ and\ Antimony\ Free.}$
- 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
- $3.\ Product\ manufactured\ with\ Green\ Molding\ Compound\ and\ does\ not\ contain\ Halogens\ or\ Sb_2O_3\ Fire\ Retardants.$
- 4. For packaging details, go to our website at http://www.diodes.com.

Marking Information



22N = Marking Code YM = Date Code Marking Y = Year (ex: U = 2007) M = Month (ex: 9 = September)

Date Code Key

	,												
Year	2007	2008	2009	2010	201	1	2012	20	013	2014	2015	2016	2017
Code	U	V	W	X	Υ		Z		Α	В	С	D	Е
Month	Jan	Feb	Mar	Apr	May	Jun	J	ul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6		7	8	9	0	N	D



Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V_{DSS}	20	V
Gate-Source Voltage	V_{GSS}	±12	V
Drain Current (Note 5)	I _D	2.0	Α
Pulsed Drain Current (Note 6)	I _{DM}	7	Α

Thermal Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P_{D}	600	mW
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	208	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

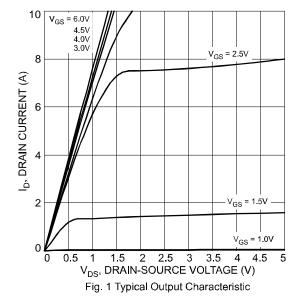
Electrical Characteristics @T_A = 25°C unless otherwise specified

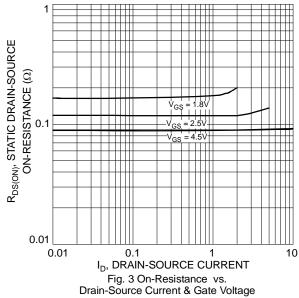
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	20	_		V	$V_{GS} = 0V, I_D = 10\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}			1	μА	$V_{DS} = 20V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}			±10	μΑ	$V_{GS} = \pm 12V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(th)}	0.5	_	1.0	V	$V_{DS} = V_{CS}, I_D = 250 \mu A$	
		_	81 113 170	110		$V_{GS} = 4.5V, I_D = 2.5A$	
Static Drain-Source On-Resistance	R _{DS (ON)}			145	mΩ	$V_{GS} = 2.5V, I_D = 1.5A$	
				230		$V_{GS} = 1.8V, I_D = 1.0A$	
Forward Transfer Admittance	Y _{fs}		5		S	$V_{DS} = 5V, I_{D} = 2.4A$	
Diode Forward Voltage (Note 7)	V_{SD}		0.8	1.1	V	$V_{GS} = 0V, I_S = 1.05A$	
DYNAMIC CHARACTERISTICS							
Input Capacitance	C _{iss}		188	_	pF		
Output Capacitance	Coss		44		pF	$V_{DS} = 10V$, $V_{GS} = 0V$ f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}		30	_	pF	I = 1.0IVII IZ	
Total Gate Charge	Q_{g}		2.3	_	nC		
Gate-Source Charge	Qgs		0.3		nC	$V_{DS} = 10V, I_D = 11.6A$	
Gate-Drain Charge	Q_{gd}	_	0.5		nC		
Turn-On Delay Time	t _{d(on)}	_	8				
Rise Time	t _r	_	3.8	_	ns	$V_{DD} = 10V$, $R_L = 10\Omega$	
Turn-Off Delay Time	t _{d(off)}	_	19.6	_	115	$I_D = 1A, V_{GEN} = 4.5V, R_G = 6\Omega$	
Fall Time	t _f	_	8.3	_			

Notes:

- 5. Device mounted on FR-4 PCB, or minimum recommended pad layout
- Sepetitive rating, pulse width limited by junction temperature.
 Short duration pulse test used to minimize self-heating effect.







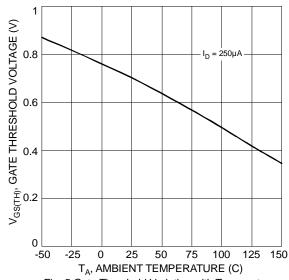
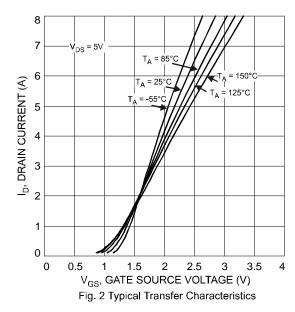


Fig. 5 Gate Threshold Variation with Temperature



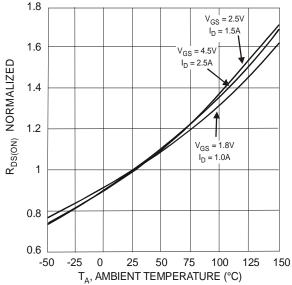
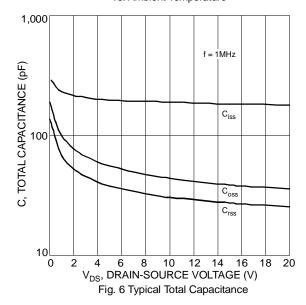
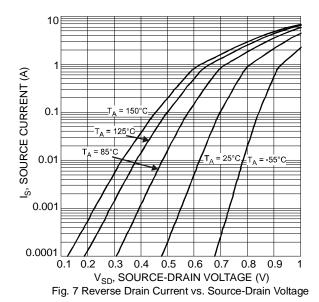
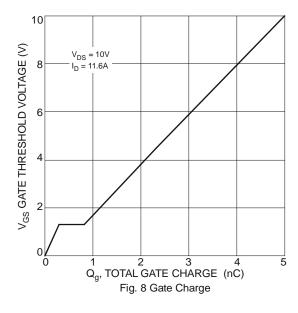


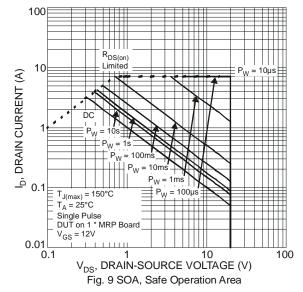
Fig. 4 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature



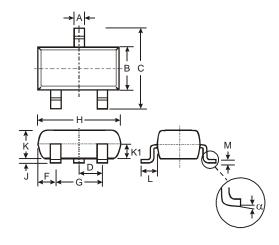








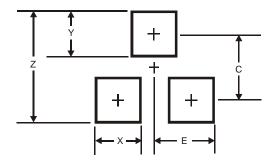
Package Outline Dimensions



SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
C	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Η	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.903	1.10	1.00				
K1	-	-	0.400				
L	0.45	0.61	0.55				
M	0.085	0.18	0.11				
α	0°	8°	-				
All Dimensions in mm							



Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Υ	0.9
С	2.0
E	1.35

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